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Lead-free Green

DMN10H6D2LFDB

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
100V	6Ω @ V_{GS} = 10V	0.27A
	10Ω @ V_{GS} = 4.5V	0.21A

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- **ESD Protected Up to 1kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Switching Applications

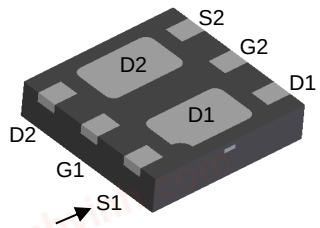
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

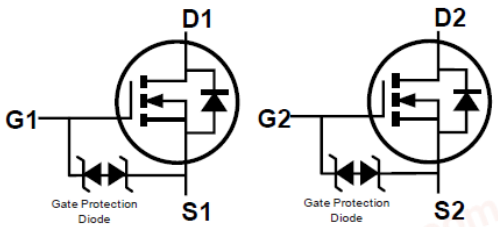


ESD Protected

U-DFN2020-6 (Type B)



Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H6D2LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN10H6D2LFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information

U-DFN2020-6 (Type B)



62 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 1 = 2021)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	0.27 0.22	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.27	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	0.6	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	0.6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	178	°C/W
Total Power Dissipation (Note 6)		P_D	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	120	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	2.0	V	V_{DS} = V_{GS}, I_D = 1mA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.4 3.6	6 10	Ω	V_{GS} = 10V, I_D = 0.19A V_{GS} = 4.5V, I_D = 0.15A
Diode Forward Voltage	V_{SD}	—	0.9	1.3	V	V_{GS} = 0V, I_S = 0.34A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	41	—	pF	V_{DS} = 50V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	4.2	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	3.1	—	pF	
Gate Resistance	R_g	—	35	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	0.6	—	nC	V_{DS} = 30V, I_D = 1A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	1.2	—	nC	
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.0	—	ns	V_{DD} = 50V, V_{GS} = 10V, R_g = 6Ω, I_D = 0.19A
Turn-On Rise Time	t_R	—	2.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	9.7	—	ns	
Turn-Off Fall Time	t_F	—	9.2	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	31	—	ns	I_F = 1A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	—	19	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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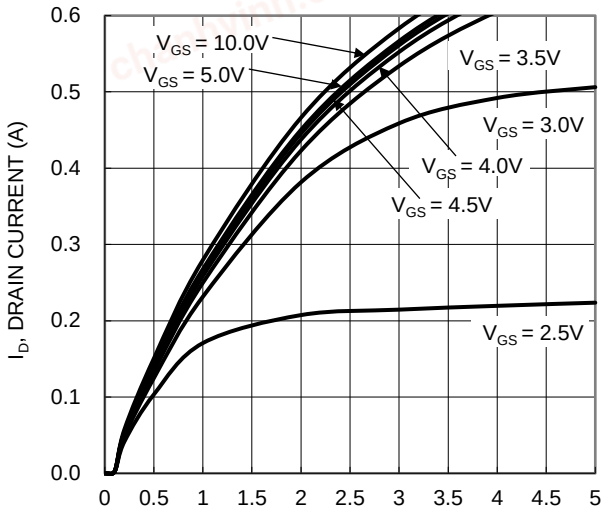


Figure 1. Typical Output Characteristic

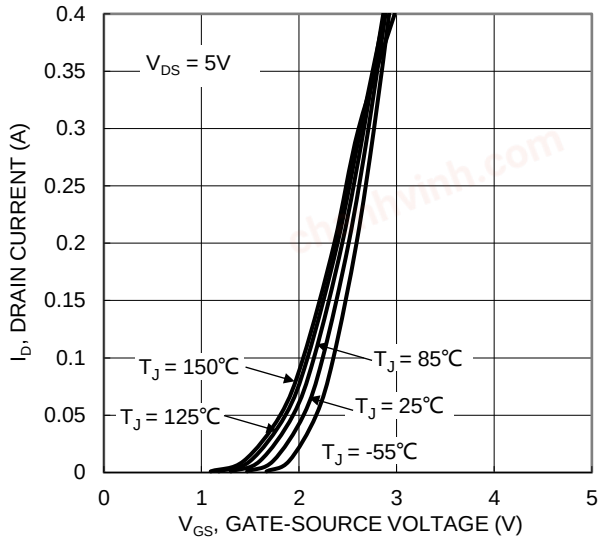


Figure 2. Typical Transfer Characteristic

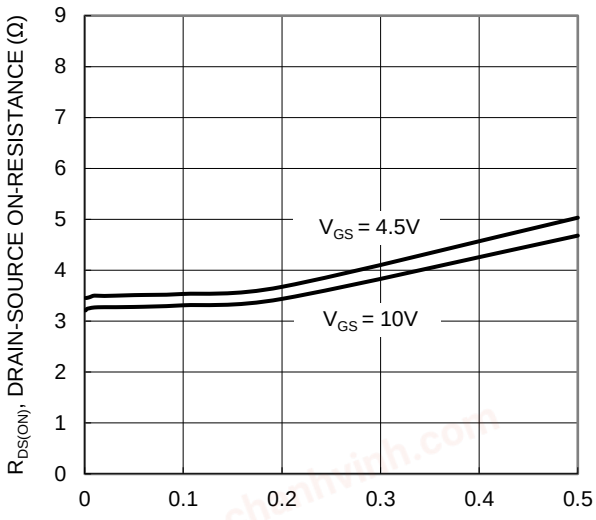


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

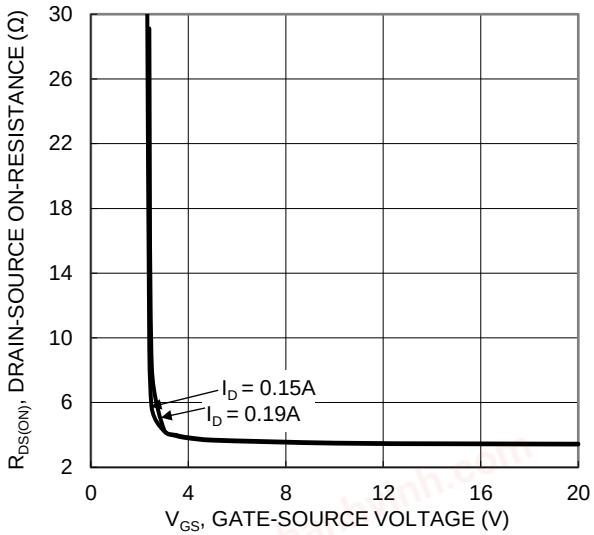


Figure 4. Typical Transfer Characteristic

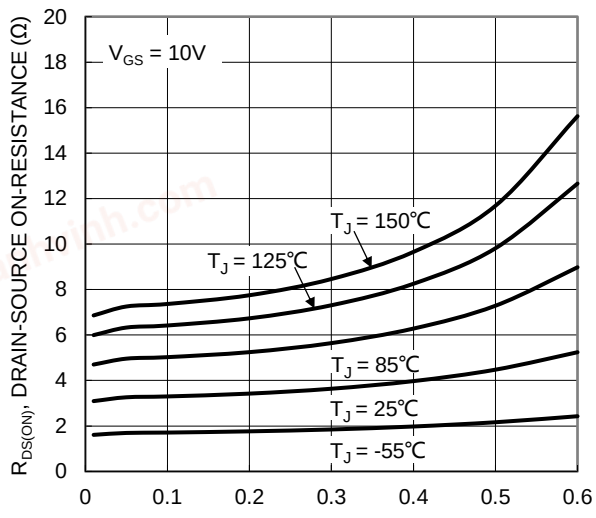


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

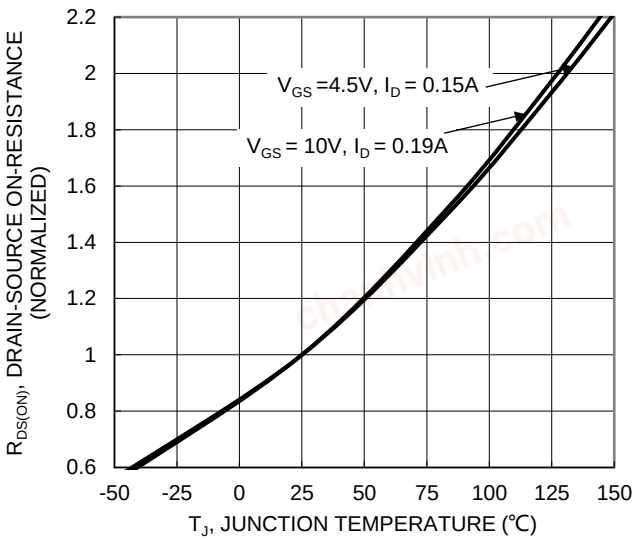


Figure 6. On-Resistance Variation with Junction Temperature

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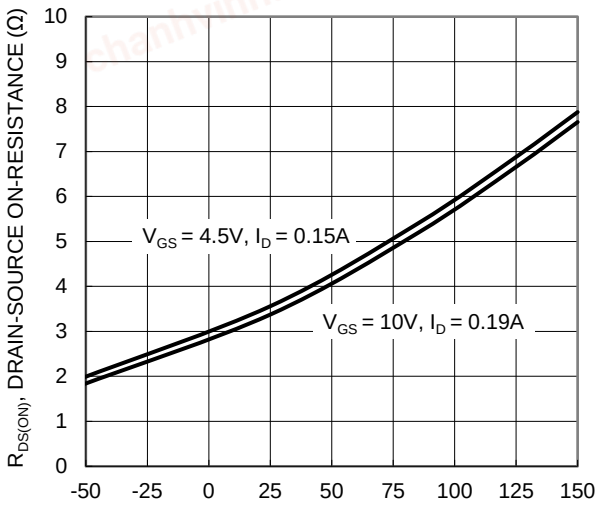


Figure 7. On-Resistance Variation with Junction Temperature

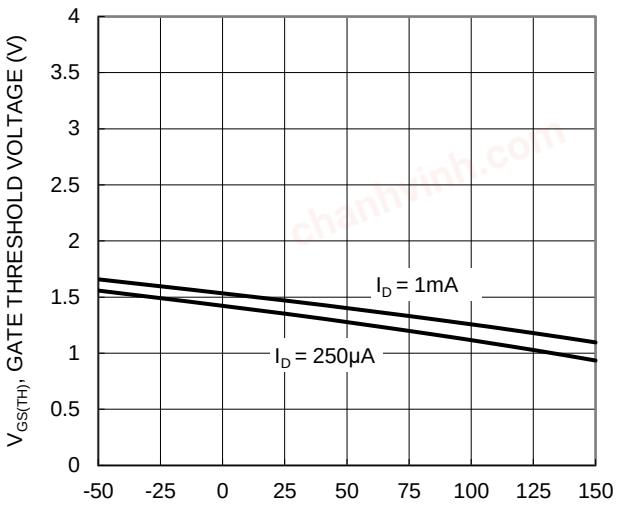


Figure 8. Gate Threshold Variation vs. Junction Temperature

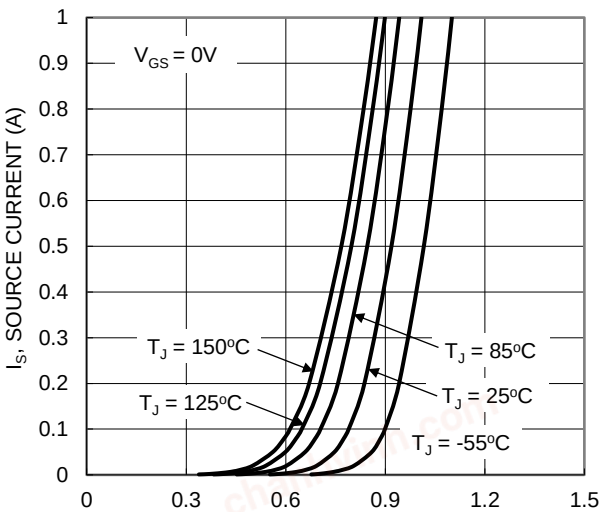


Figure 9. Diode Forward Voltage vs. Current

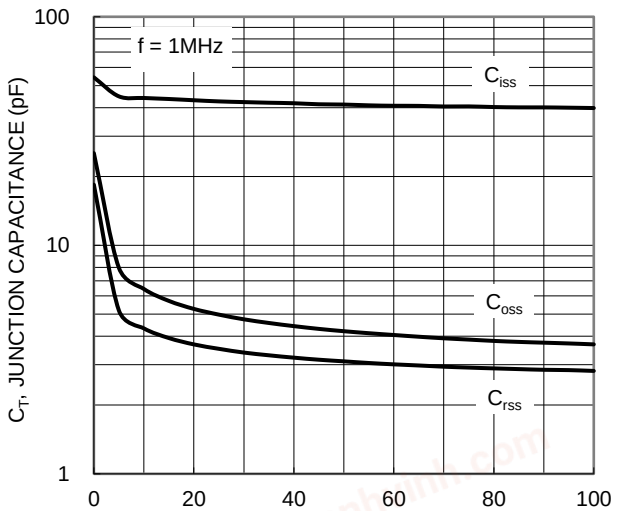


Figure 10. Typical Junction Capacitance

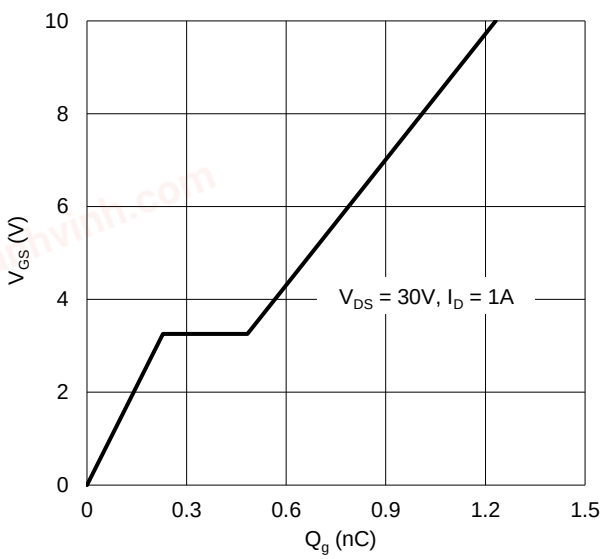


Figure 11. Gate Charge

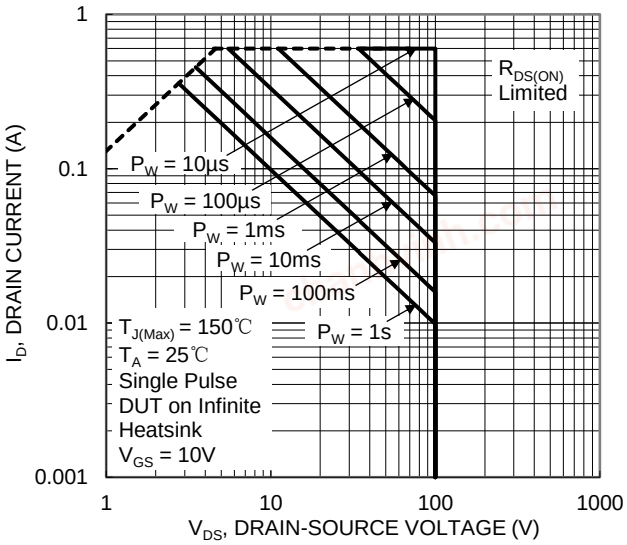


Figure 12. SOA, Safe Operation Area

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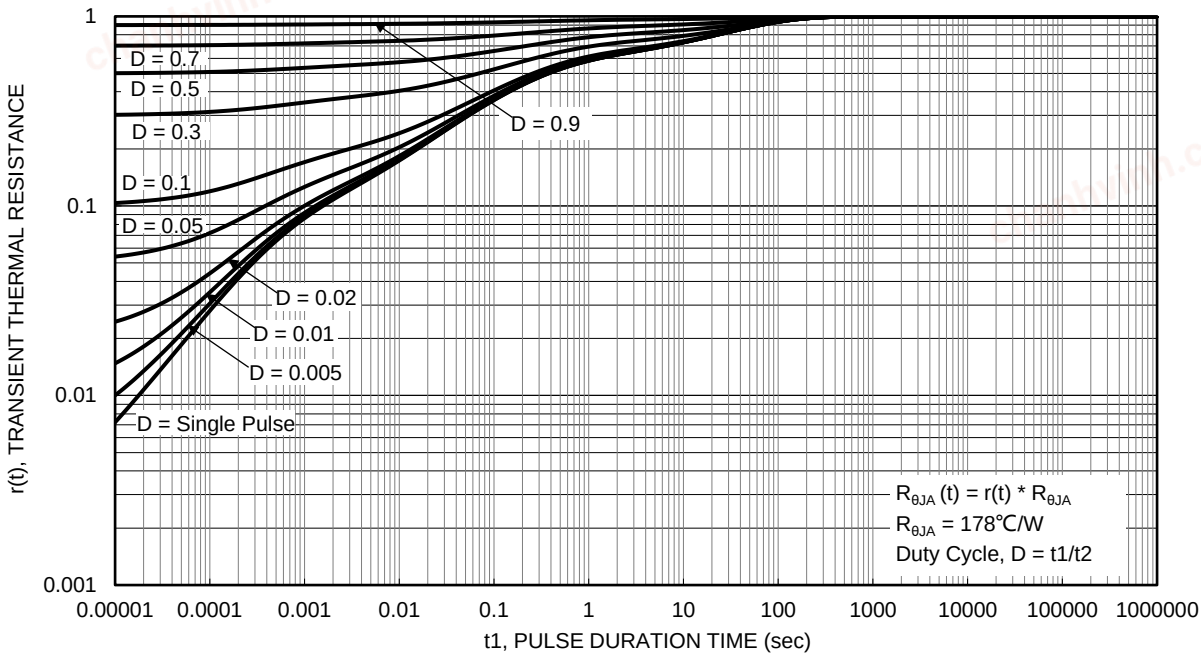


Figure 13. Transient Thermal Resistance

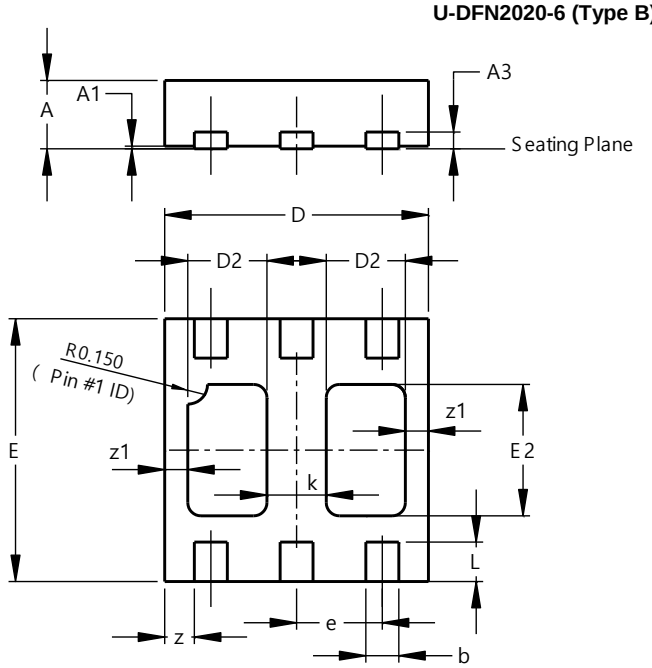
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

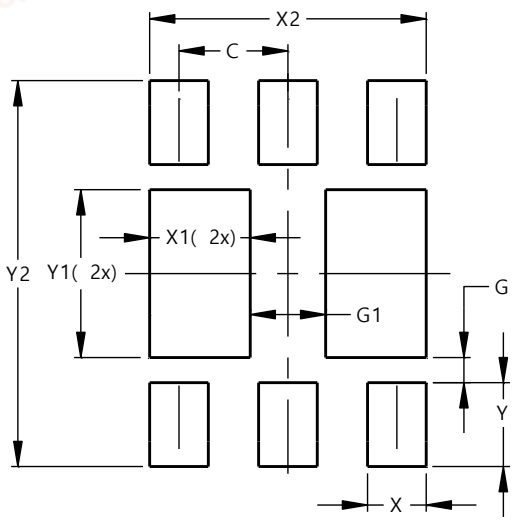


U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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